

TC74HC109AP, TC74HC109AF, TC74HC109AFN**DUAL J- \bar{K} FLIP-FLOP WITH PRESET AND CLEAR**

The TC74HC109A is a high speed CMOS J- \bar{K} FLIP FLOP fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

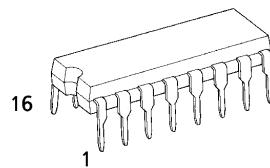
In accordance with the logic levels applied to the J and \bar{K} inputs, the outputs change state on the positive going transition of the clock pulse.

$\overline{\text{CLR}}$ and $\overline{\text{PR}}$ are independent of the clock and are accomplished by a low logic level on the corresponding input. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

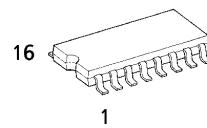
FEATURES :

- High Speed..... $f_{\text{MAX}} = 63\text{MHz}$ (typ.) at $V_{\text{CC}} = 5\text{V}$
- Low Power Dissipation..... $I_{\text{CC}} = 2\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{\text{NIH}} = V_{\text{NIL}} = 28\% V_{\text{CC}}$ (Min.)
- Output Drive Capability.....10 LSTTL Loads
- Symmetrical Output Impedance..... $|I_{\text{OH}}| = I_{\text{OL}} = 4\text{mA}(\text{Min.})$
- Balanced Propagation Delays..... $t_{\text{PLH}} \approx t_{\text{PHL}}$
- Wide Operating Voltage Range..... $V_{\text{CC}} (\text{opr.}) = 2\text{V} \sim 6\text{V}$
- Pin and Function Compatible with 74LS109

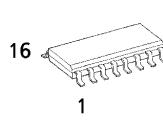
(Note) The JEDEC SOP (FN) is not available in Japan.



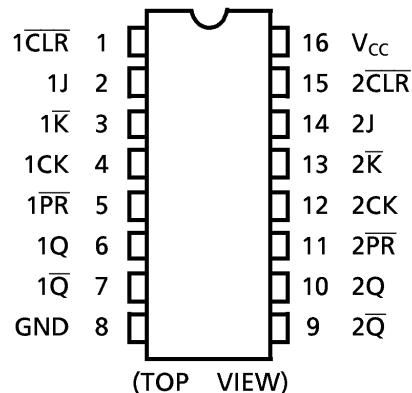
P (DIP16-P-300-2.54A)
Weight : 1.00g (Typ.)



F (SOP16-P-300-1.27)
Weight : 0.18g (Typ.)

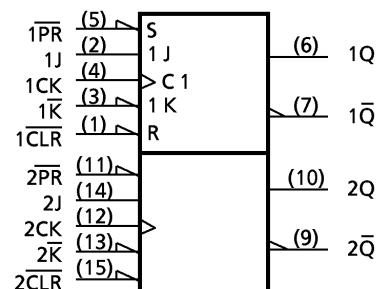


FN (SOL16-P-150-1.27)
Weight : 0.13g (Typ.)

PIN ASSIGNMENT**TRUTH TABLE**

INPUTS					OUTPUTS		FUNCTION
CLR	$\overline{\text{PR}}$	J	\bar{K}	CK	Q	\bar{Q}	
L	H	X	X	X	L	H	CLEAR
H	L	X	X	X	H	L	PRESET
L	L	X	X	X	H	H	
H	H	L	H	↓	Q_n	\bar{Q}_n	NO CHANGE
H	H	L	L	↓	L	H	
H	H	H	H	↓	H	L	
H	H	H	L	↓	\bar{Q}_n	Q_n	TOGGLE
H	H	X	X	↓	Q_n	\bar{Q}_n	NO CHANGE

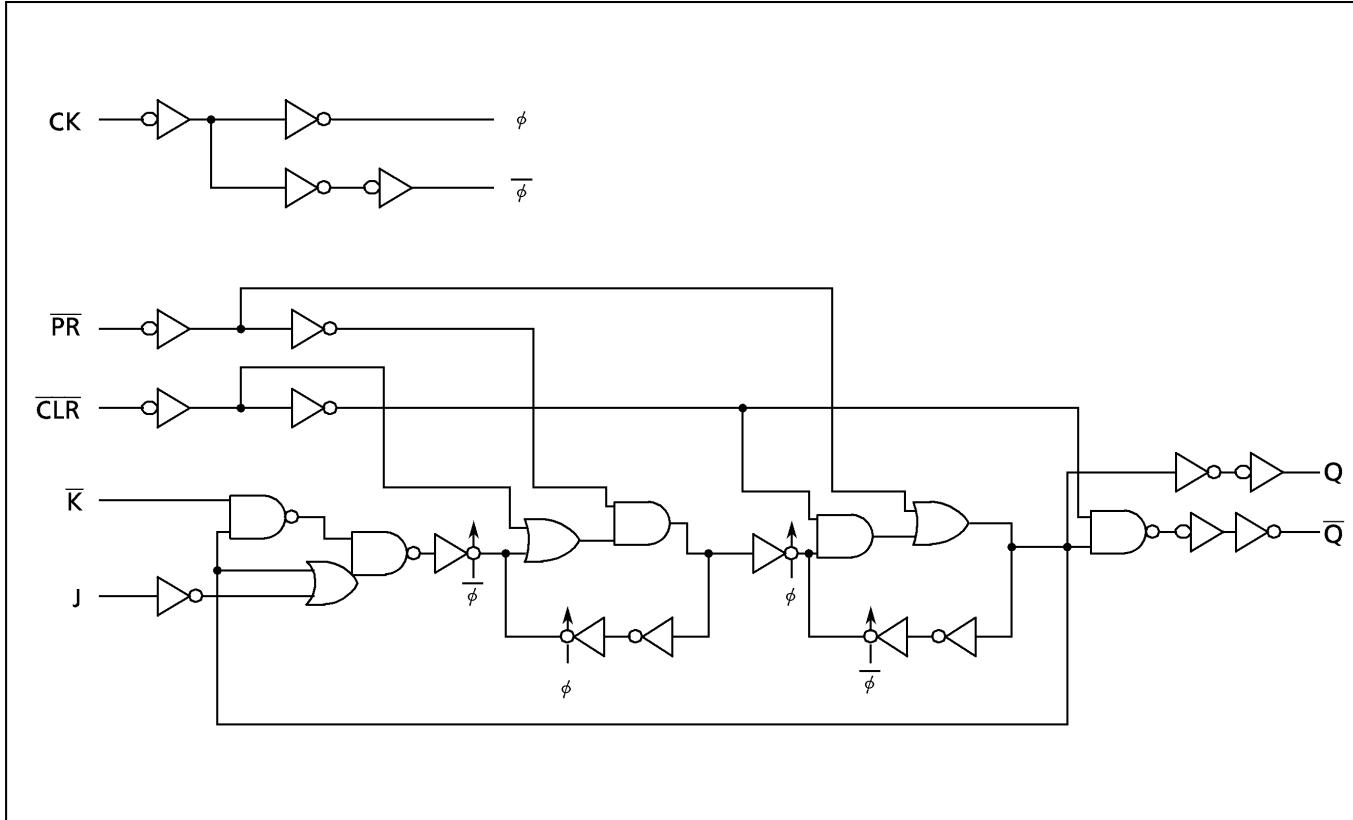
X : Don't Care

IEC LOGIC SYMBOL

980508EBA2

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SYSTEM DIAGRAM



980508EBA2'

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} / Ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{STG}	-65~150	°C

*500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$. From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2~6	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	t_r, t_f	0~ 1000 ($V_{CC} = 2.0\text{V}$) 0~ 500 ($V_{CC} = 4.5\text{V}$) 0~ 400 ($V_{CC} = 6.0\text{V}$)	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V_{IH}		2.0	1.50	—	—	1.50	—	V
			4.5	3.15	—	—	3.15	—	
			6.0	4.20	—	—	4.20	—	
Low - Level Input Voltage	V_{IL}		2.0	—	—	0.50	—	0.50	V
			4.5	—	—	1.35	—	1.35	
			6.0	—	—	1.80	—	1.80	
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -20\mu\text{A}$	2.0	1.9	2.0	—	1.9	V
			$I_{OH} = -4\text{ mA}$	4.5	4.4	4.5	—	4.4	
			$I_{OH} = -5.2\text{ mA}$	6.0	5.9	6.0	—	5.9	
				4.5	4.18	4.31	—	4.13	
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 20\mu\text{A}$	6.0	5.68	5.80	—	5.63	V
			$I_{OL} = 4\text{ mA}$	2.0	—	0.0	0.1	—	
			$I_{OL} = 5.2\text{ mA}$	4.5	—	0.0	0.1	—	
				6.0	—	0.0	0.1	—	
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	± 0.1	—	± 1.0	μA
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	2.0	—	20.0	

TIMING REQUIREMENTS (Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}(\text{V})$	$T_a = 25^\circ\text{C}$		$T_a = -40\text{--}85^\circ\text{C}$	UNIT
				TYP.	LIMIT	LIMIT	
Minimum Pulse Width (CK)	$t_{W(L)}$		2.0	—	75	95	ns
	$t_{W(H)}$		4.5	—	15	19	
			6.0	—	13	16	
Minimum Pulse Width ($\overline{\text{PR}}$, $\overline{\text{CLR}}$)	$t_{W(L)}$		2.0	—	75	95	ns
			4.5	—	15	19	
			6.0	—	13	16	
Minimum Set-up Time	t_s		2.0	—	75	95	ns
			4.5	—	15	19	
			6.0	—	13	16	
Minimum Hold Time	t_h		2.0	—	0	0	ns
			4.5	—	0	0	
			6.0	—	0	0	
Minimum Removal Time ($\overline{\text{PR}}$, $\overline{\text{CLR}}$)	t_{rem}		2.0	—	50	65	ns
			4.5	—	10	13	
			6.0	—	9	11	
Clock Frequency	f		2.0	—	6	5	MHz
			4.5	—	31	25	
			6.0	—	36	29	

AC ELECTRICAL CHARACTERISTICS ($C_L = 15\text{pF}$, $V_{CC} = 5\text{V}$, $T_a = 25^\circ\text{C}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}(\text{V})$	MIN.	TYP.	MAX.	UNIT
				—	—	—	
Output Transition Time	t_{TLH}		2.0	—	6	12	ns
	t_{THL}		4.5	—	—	—	
			6.0	—	—	—	
Propagation Delay Time (CK-Q, \overline{Q})	t_{PLH}		2.0	—	13	26	ns
	t_{PHL}		4.5	—	—	—	
			6.0	—	—	—	
Propagation Delay Time ($\overline{\text{PR}}$, $\overline{\text{CLR}}-\text{Q}, \overline{Q}$)	t_{PLH}		2.0	—	13	26	ns
	t_{PHL}		4.5	—	—	—	
			6.0	—	—	—	
Maximum Clock Frequency	f_{MAX}		2.0	33	63	—	MHz

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}(\text{V})$	$T_a = 25^\circ\text{C}$		$T_a = -40\text{--}85^\circ\text{C}$		UNIT	
				MIN.	TYP.	MAX.	MIN.		
Output Transition Time	t_{TLH}		2.0	—	30	75	—	95	ns
	t_{THL}		4.5	—	8	15	—	19	
			6.0	—	7	13	—	16	
Propagation Delay Time (CK-Q, Q)	t_{PLH}		2.0	—	50	150	—	190	ns
	t_{PHL}		4.5	—	16	30	—	38	
			6.0	—	13	26	—	32	
Propagation Delay Time ($\overline{\text{PR}}$, $\overline{\text{CLR}}-\text{Q}, \overline{Q}$)	t_{PLH}		2.0	—	50	150	—	190	ns
	t_{PHL}		4.5	—	16	30	—	38	
			6.0	—	13	26	—	32	
Maximum Clock Frequency	f_{MAX}		2.0	6	17	—	5	—	MHz
			4.5	31	59	—	25	—	
			6.0	36	67	—	29	—	
Input Capacitance	C_{IN}		2.0	—	5	10	—	10	pF
Power Dissipation Capacitance	$C_{PD}(1)$		2.0	—	41	—	—	—	

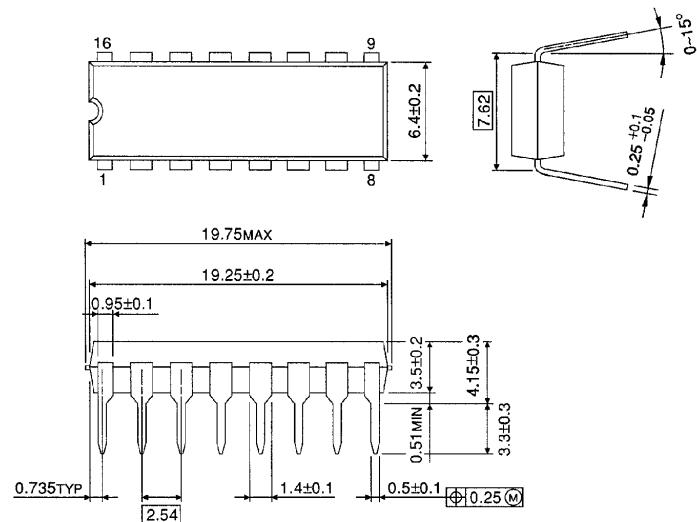
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(\text{opr})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2 \text{ (per F/F)}$$

DIP 16PIN OUTLINE DRAWING (DIP16-P-300-2.54A)

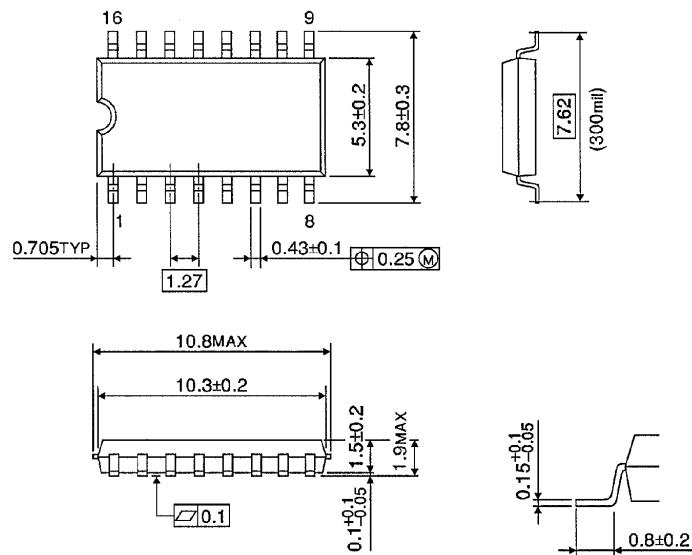
Unit in mm



Weight : 1.00g (Typ.)

SOP 16PIN (200mil BODY) OUTLINE DRAWING (SOP16-P-300-1.27)

Unit in mm

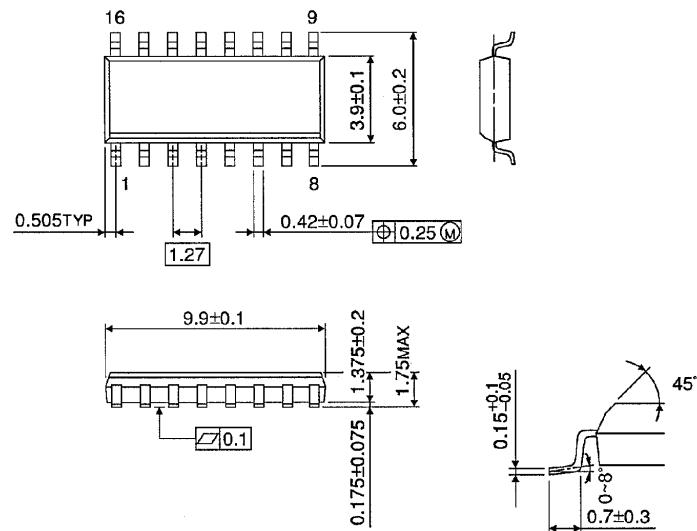


Weight : 0.18g (Typ.)

SOP 16PIN (150mil BODY) OUTLINE DRAWING (SOL14-P-150 -1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.13g (Typ.)